

(19) World Intellectual Property
Organization
International Bureau



(43) International Publication Date
16 December 2004 (16.12.2004)

PCT

(10) International Publication Number
WO 2004/109749 A2

(51) International Patent Classification⁷: **H01L**

(21) International Application Number:
PCT/IL2004/000501

(22) International Filing Date: 10 June 2004 (10.06.2004)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
60/477,400 11 June 2003 (11.06.2003) US

(81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

(84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

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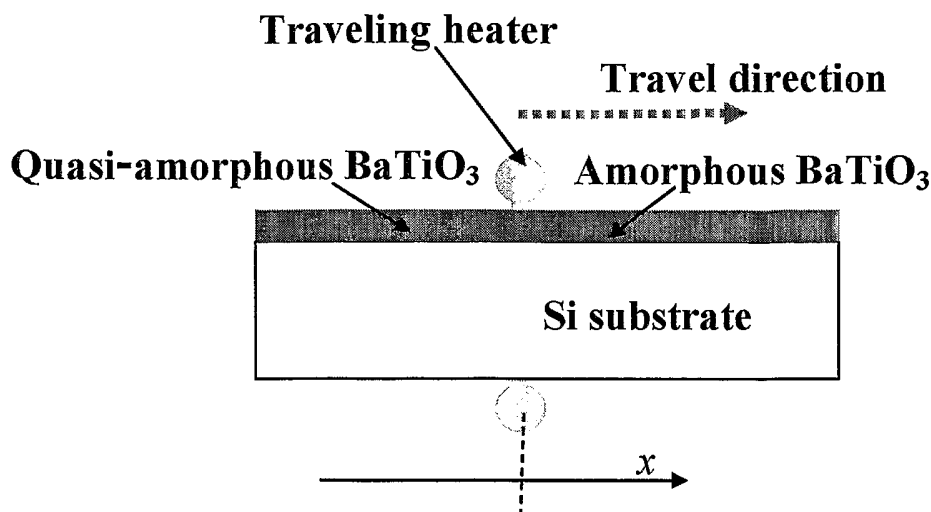
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Published:

— without international search report and to be republished upon receipt of that report

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(54) Title: PYROELECTRIC COMPOUND AND METHOD OF ITS PREPARATION



(57) Abstract: A novel pyroelectric compound is presented. The compound is inorganic, quasi-amorphous oxide compound of a metal, mixture of metals or semiconducting element.

PYROELECTRIC COMPOUND AND METHOD OF ITS PREPARATION

FIELD OF THE INVENTION

This invention relates to pyroelectric compounds, a process for their preparation and devices comprising them.

5 LIST OF REFERENCES

The following references are considered to be pertinent for the purpose of understanding the background of the present invention:

- 10 [1] S. Li, J. A. Eastman, Z. Li, C. M. Foster, R. E. Newnham, and L. E. Cross, *Phys. Lett. A* **1996**, 212, 341.
- [2] N. A. Pertsev, A. G. Zembilgotov, and A. K. Tagantsev, *Phys. Rev. Lett.* **1998**, 80, 1988.
- [3] T. Feng and J. M. Cowley, *Appl. Phys. Lett.* **1994**, 65, 1906.
- [4] M. H. Frey and D. A. Payne, *Phys. Rev. B* **1996**, 54, 3158.
- 15 [5] G. Ayton, M. J. P. Gingras, and G. N. Patey, *Phys. Rev. Lett.* **1995**, 75, 2360.
- [6] P. J. Grout, N. H. March, and Y. Ohmura, *Appl. Phys. Lett.* **1978**, 32, 453.
- [7] A. A. Bahgat and T. M. Kamel, *Phys. Rev. B* **2001**, 63, art. no.
- [8] A. M. Glass, M. E. Lines, K. Nassau, and J. W. Shiever, *Appl. Phys. Lett.* **1977**, 31, 249.
- 20 [9] Y. H. Xu, C. H. Cheng, and J. D. Mackenzie, *J Non-Cryst Solids* **1994**, 176, 1.
- [10] B. K. Tanner, *X-ray diffraction topography*, Pergamon Press., Oxford **1976**.
- [11] K. Sreenivas, A. Mansingh, and M. Sayer, *J. Appl. Phys.* **1987**, 62, 4475.
- [12] B. S. Chiou and M. C. Lin, *Thin Solid Films* **1994**, 248, 247.
- [13] W. T. Liu, S. T. Lakshmikumar, D. B. Knorr, E. J. Rymaszewski, T. M. Lu, and
25 H. Bakhru, *Appl. Phys. Lett.* **1995**, 66, 809.
- [14] M. N. Kamalasanan, N. D. Kumar, and S. Chandra, *J. Appl. Phys.* **1994**, 76, 4603.

- 2 -

- [15] A. A. Lipovskii, D. K. Tagantsev, A. A. Vetrov, and O. V. Yanush, *Optical Materials* **2003**, 21, 749.
- [16] D. J. Johns, *Thermal stress analysis*, Pergamon, Oxford **1965**.
- [17] A. K. Tagantsev, *Phase Transitions* **1991**, 35, 119.
- 5 [18] W. L. Warren, G. E. Pike, K. Vanheusden, D. Dimos, B. A. Tuttle, and J. Robertson, *J. Appl. Phys.* **1996**, 79, 9250.
- [19] D. M. Kozuch, M. Stavola, S. J. Spector, S. J. Pearton, and J. Lopata, *Phys. Rev. B* **1993**, 48, 8751.
- [20] L. Nam-Yang, T. Sekine, Y. Ito, and K. Uchino, *Jpn. J. Appl. Phys. 1.* **1994**, 33, 1484.
- 10 [21] R. M. A. Azzam, *Ellipsometry and polarized light*, North-Holland, Amsterdam **1987**.
- [22] G. G. Stoney, *Proc. R. Soc. London* **1909**, A82, 172.
- [23] A. G. Chynoweth, *Appl. Phys. Lett.* **1956**, 27, 78.
- 15 [24] B. R. Holeman, *Infrared Physics* **1972**, 12, 125.
- [25] N. Stavitski, V. Lyahovitskaya, J. Nair, I. Zon, R. Popovitz-Biro, E. Wachtel, Y. Feldman, and I. Lubomirsky, *Appl. Phys. Lett.* **2002**, 81, 4177.
- [26] M. E. Lines and A. M. Glass, *Principles and applications of ferroelectrics and related materials.*, Clarendon Press, Oxford **2001**.
- 20 [27] O. Kolosov, A. Gruverman, J. Hatano, K. Takahashi, and H. Tokumoto, *Phys. Rev. Lett.* **1995**, 74, 4309.
- [28] Robertson, J. Warren, W.L. & Tuttle, B.A. in *Journal of Applied Physics* 3975-3980 (1995).
- [29] Ayton, G. Gingras, M.J.P. & Patey, G.N. Ferroelectric and dipolar glass phases of noncrystalline systems. *Phys. Rev. E* 56, 562-570 (1997).
- 25 [30] Baghat, A.A. & Kamel, T.M. Possible observation of a glassy ferroelectric: $\text{Bi}_{1.8}\text{Pb}_{0.2}\text{Sr}_2\text{Ca}_2\text{Cu}_{2.8}\text{K}_{0.2}\text{O}_z$. *Phys. Rev. B* **63**, art. no. – 012101 (2001).
- [31] DE 10028022;
- [32] US 5,504,330.

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BACKGROUND OF THE INVENTION

Pyroelectricity is a property of certain crystals consisting of polarization developed in a crystal by an inequality of temperature. Spontaneous or stress-induced polarization, signifying pyroelectricity and piezoelectricity respectively, can appear in ionic solids solely due to a non-centrosymmetrical spatial distribution of ions in a polar crystalline structure. Although theory does not impose strict limitations on the size of a polar crystallite^[1,2], the magnitude of pyroelectric and piezoelectric effects of some ceramics, particularly BaTiO₃, rapidly decrease as grain size diminishes to a few nanometers^[1,3,4].

10 Determination of the minimal number of periodically arranged unit cells for which a crystal retains pyroelectric and piezoelectric properties has become increasingly important due to the rapid incorporation of these materials into nanometer-scale devices.

As disclosed in U.S. Patent No. 5,504,330, pyroelectric properties of a thin film made of perovskite materials may be enhanced, by the addition of lead to an original perovskite material having an original ferroelectric critical grain size, and then forming a layer of the lead enhanced perovskite material having an average grain size less than the original ferroelectric critical grain size. The remanent polarization of the layer appeared to be substantially greater than the remanent polarization of the original perovskite material.

Thin BaTiO₃ ferroelectric films are important for a number of applications such as high charge density capacitors, ferroelectric memory, and microwave and optoelectronic devices. However, integration of BaTiO₃ into Si microfabrication technology is hindered by the high chemical reactivity of BaTiO₃ with respect to Si. Therefore, despite the small misfit between the lattice parameter of Si and inter-plane distance of BaTiO₃, epitaxial growth of BaTiO₃ on Si always requires intermediate buffer layers.

DE 10028022 discloses the production of highly ordered low molecular inorganic thin action layers at low temperature on silicon chips in pyroelectric

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detectors. Such production comprises applying an action layer made from a ferroelectric, pyroelectric or piezoelectric material to a substrate with a highly ordered polytetrafluoroethylene coating whereby the action layer is ordered through the polytetrafluoroethylene substrate.

5 It is also known that pyro- and piezo-electric effects may exist in structures that lack the spatial periodicity inherent for ionic crystals, but composed of polar molecules with directional ordering. An example of such a material is a nematic liquid crystal. Spontaneous or stress induced dipole ordering without fine-tuned positional order is theoretically possible in ionic
10 solids^[5] as well; however only indirect experimental evidence supporting this theory has been presented so far ^[6-9].

SUMMARY OF THE INVENTION

The present invention provides for novel pyroelectric (and consequently
15 piezoelectric) compound and a method of its preparation.

The compound of the present invention, while being inorganic, shows clear pyroelectric and piezoelectric properties despite the lack of spatial periodicity inherent to ionic crystals.

The inventor has surprisingly found that a quasi-amorphous compound
20 having a relatively low dielectric constant and a relatively high pyroelectricity may be produced, by subjecting an amorphous compound to a mechanical strain, where the mechanical strain does not promote the formation of crystallites within the quasi-amorphous compound. The compound obtained in the present invention is thus characterized by the advantageous features of amorphous compounds (e.g.,
25 low dielectric constant, low production costs) and the advantageous features of crystalline compounds (e.g., pyroelectricity and piezoelectricity). The pyroelectric and piezoelectric effects of the quasi-amorphous compound of the invention may be attributed to a spontaneous local dipole ordering, which is usually observed in crystalline solids but not in amorphous ones.

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The term "*quasi amorphous compound*" should be construed herein as a compound which is a non crystalline ionic solid having a macroscopic polarization. The polarization manifests itself as pyroelectric effect.

Thus, according to the first aspect thereof, the present invention provides a
5 novel pyroelectric compound having an amorphous ionic solid structure with directional polar ordering. More specifically, the present invention provides an inorganic, quasi-amorphous oxide compound of a metal, mixture of metals or semiconducting element, the compound having pyroelectric properties.

According to a preferred embodiment of the invention, the oxide
10 compound has the formula $(A_xB_{1-x})_pO_n$, wherein A and B are independently selected from transition metals, elements of Group IVA of the periodic table, alkali metals, alkali earth metals and rare earth metals; x has values of between 0 to 1; p is an integer having the values 1, 2 or 3; and n is an integer having the value of 1, 2, 3 or 4. Preferably, A is a transition metal or an element of Group IVA of the periodic
15 table; x is 1 and p is 2. More preferably, the compound is selected from SiO_2 and TiO_2 .

According to another preferred embodiment of the invention, the compound has the formula $(A_xB_{1-x})(C_yD_{1-y})O_n$ wherein A and B are independently selected from alkali metals, alkali earth metals, rare earth metals and elements of
20 Group IVA of the periodic table; C and D are independently selected from transition metals and alkali earth metals; x and y have values of between 0 to 1; and n is an integer having a value between 1 to 10. Preferably, n has a value of 1, 2, 3 or 4 and more preferably n is 1, 2 or 3.

According to a preferred embodiment of the invention, A and B are
25 independently selected from Ba, Sr, Ca, Pb, La, Eu, Li, Na, K and Cs ; C and D are independently selected from Ti, Zr, Nb, Ta, Sc, Mg and V; and n is 3.

Preferably, A and B are independently selected from Ba, Sr, Ca, Pb, La and Eu.

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According to another preferred embodiment, A and B are independently selected from Li, Na, K and Cs.

Similarly, C and D are independently selected from Ti and Zr. According to another preferred embodiment, C and D are independently selected Nb, Ta, Sc, Mg and V.

According to a further preferred embodiment, in the quasi-amorphous compound of the invention, $y=0$, thus obtaining a compound of the formula $(A_xB_{1-x})DO_3$ having pyroelectric properties, wherein A, B, D and x have the meanings defined above.

Specific examples of pyroelectric compounds according to the present invention are $BaTiO_3$, $CaTiO_3$, $PbTiO_3$, $Pb(ZrTi)O_3$, $Pb(Zr_{0.35}Ti_{0.65})O_3$, $(PbCa)TiO_3$, $(PbLa)(ZrTi)O_3$, $PbLaTiO_3$, $Pb(ScTa)O_3$, $Pb(ScNb)O_3$, $Pb(MgNb)O_3$, $SrTiO_3$, $(Sr_{0.65},Ba_{0.35})TiO_3$, $(Ba_{0.70},Sr_{0.30})TiO_3$ and $EuTiO_3$. Preferably, the compound is selected from $BaTiO_3$, $PbTiO_3$ and $SrTiO_3$. More preferably, the compound is $BaTiO_3$.

The compound of the present invention has a pyroelectricity in the range from about 10^{-12} C/(cm² x K) to about 10^{-7} C/(cm² x K).

According to another aspect, the present invention provides a process for preparing pyroelectric compound, comprising applying a mechanical strain to a substantially amorphous compound of the formula $(A_xB_{1-x})(C_yD_{1-y})O_3$ as defined above, the mechanical strain being such as to prevent crystallization of the compound, thereby obtaining inorganic quasi-amorphous compound having pyroelectric properties. The effect of mechanical strain can be achieved by subjecting the compound to an external field such as a temperature gradient or an electrical field. In a preferred embodiment, the substantially amorphous compound has the formula $(A_xB_{1-x})DO_3$, wherein A, B, D and x have the meanings defined above

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In addition, the present invention provides an inorganic quasi-amorphous compound of the formula $(A_xB_{1-x})(C_yD_{1-y})O_3$ as defined above, preparable by the process of the present invention.

The present invention according to its yet another aspect provides a device
5 comprising the compound of the present invention which can be operable as a sensor for sensing external fields including temperature, magnetic and electric field.

The present invention also provides an acoustic wave propagation channel, as well as a birefringent medium, formed by the compound of the present invention.

The compound of the present invention can be formed as a layer coating on
10 a substrate, which can be any substance of a kind that does not cause a rapid crystallization of the amorphous compound, such as Si, SiO₂ and glass.

DESCRIPTION OF THE DRAWINGS

In order to understand the invention and to see how it may be carried out in
15 practice, preferred embodiments will now be described, by way of non-limiting examples only, with reference to the accompanying drawings, in which:

Fig. 1 is a scheme illustrating the preparation of quasi-amorphous BaTiO₃ films by passing them through a steep unidirectional temperature gradient.

Fig. 2A is the X-Ray diffraction spectra of BaTiO₃ films as deposited on
20 (100) Si (1) in comparison to the spectra of the films passed through the temperature gradient (2) and part of the film (1) heated under isothermal conditions (3). The vertical lines correspond to the standard XRD pattern of tetragonal BaTiO₃ (ICSD Collection Code 23758).

Fig. 2B is the transmission electron microscopy (TEM) image and electron
25 diffraction (ED) pattern of a BaTiO₃ film passed through the temperature gradient.

Fig. 3A shows the pyroelectric response of a 182(±10)nm thick amorphous BaTiO₃ film passed through the temperature gradient, to periodic heating by an infra-red laser. The Si substrate is 275µm thick; therefore, constant temperature establishes within about 0.2 msec after the laser switches on and off.

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Fig. 3B shows the temperature dependence of the dielectric constant (at 1 kHz) for amorphous BaTiO_3 thin film; (1) as-deposited film and (2) amorphous film passed through the temperature gradient.

Figs. 4A and 4B show scanning electron microscopy images (secondary electron mode) of, respectively, an amorphous BaTiO_3 thin film passed through the temperature gradient; the other part of the same amorphous films heated in isothermal conditions.

DETAILED DESCRIPTION OF THE INVENTION

10 The present invention provides for a novel inorganic non-crystalline oxide compound having pyroelectric and piezoelectric properties, and a method of preparation of this compound.

The method of the present invention comprises subjecting sputtered amorphous compound films to a mechanical strain. This can be implemented by
15 passing the film through a steep temperature gradient. The temperature gradient has to be carefully controlled and to be such as to prevent crystallization of the amorphous compound, thereby obtaining highly stressed amorphous films.

Suitable amorphous compound for use in the process of the present invention may be any compound that possesses piezoelectric and pyroelectric
20 properties in its crystalline form. A specific, non-limiting example of such compound is BaTiO_3 .

In the process of the present invention, a polar ionic solid is produced by alignment of local dipoles of the molecules in an amorphous compound by applying a mechanical strain. Any method that creates a mechanical strain, such
25 as electric field, temperature gradient, etc., would be suitable for achieving alignment of the local dipoles thereby forming a macroscopic dipole moment.

The highly stressed amorphous films obtained by the process of the present invention have pyroelectric and piezoelectric properties as clearly

demonstrated in the experimental section below. In addition, the obtained films have a low dielectric constant (~ 30) and a cheap producing cost.

Thus, the obtained films represent a polar ionic solid without spatial periodicity and therefore, should be henceforth referred to as quasi-amorphous.

5 Without being bound to theory, a possible mechanism for the formation of polarity in the obtained quasi-amorphous BaTiO_3 thin films probably includes sharp increase of the dielectric constant during the transformation of the amorphous into the quasi-amorphous films and implies molecular grouping, which is formation of crystal motifs. Crystal motifs earlier observed in electro-
10 optic glasses can be viewed as regions with a local crystal-like symmetry that gradually vanishes within 2-3 coordination spheres ^[15].

The steep temperature gradient during formation of the quasi-amorphous films generates a gradient of mechanical strain ^[16] that poles the films due to the flexoelectric effect ^[17]. The strain gradient has two components: in-plane (along
15 the temperature gradient), and out-of-plane (a result of the clamping caused by the cold part of the film) ^[16]. The latter component is responsible for the out-of-plane orientation of the crystal motifs in the films. Thus, if the crystal motifs are polar, their partial orientation creates a sense of polarity in a quasi-amorphous film as a whole. Once formed, the motifs cannot change their orientation due to
20 the large in-plane compressive stress ^[18,19].

A possible mechanism that may provide considerable thermal stability for the obtained quasi-amorphous thin films of BaTiO_3 is that nucleation of crystalline BaTiO_3 preferably occurs in a low-density intermediate phase that forms as a result of a large volume expansion of the as-deposited amorphous
25 phase. Thus, formation of a low-density intermediate phase is seen as a precondition for nucleation and crystallization. In the absence of external mechanical constraints volume expansion is unobstructed and nucleation proceeds freely.

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In a thin film clamped by a substrate, volume expansion is restricted and nucleation may be completely suppressed. This indeed occurs if an as-deposited amorphous film is pulled through a temperature gradient. The obtained quasi-amorphous phase retains thermal stability as long as the mechanical constraints are in place.

According to the mechanism suggested above, two preconditions for the formation and stability of the quasi-amorphous phase are required: a) small enthalpy of crystallization; and b) large volume expansion upon heating prior to crystallization.

Thus as-deposited films of amorphous ionic oxides which satisfy these requirements could potentially form the quasi-amorphous state if pulled through a temperature gradient. Variation of mechanical constraints may produce an indefinitely large number of quasi-amorphous phases with different density.

Combination of strong pyroelectric and piezoelectric effects with low dielectric constant indicates that quasi-amorphous compounds of the present invention are very promising for practical applications. It is important to note that the ratio of pyroelectric coefficient/dielectric constant for quasi-amorphous BaTiO_3 , as demonstrated in the experimental section is close to or surpasses that of LiNbO_3 , making it very attractive for pyroelectric detector applications. The compound of the present invention can thus be used as sensor device for sensing an external temperature or electric field to which the compound is exposed, as an acoustic wave propagation channel (being thus useful as a constructional component of a phone device), as a birefringent medium in optical devices, etc.

EXPERIMENTAL

Reference is now made to **Fig. 1** illustrating the preparation of quasi-amorphous BaTiO_3 . Amorphous 150-250 nm thick BaTiO_3 layers were deposited by radio frequency (RF) magnetron oxygen plasma sputtering^[20] on highly conductive (As-doped, 1-5 $\text{m}\Omega\cdot\text{cm}$) (100) Si wafers. As-deposited films of BaTiO_3

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were passed at a rate of 2-5 mm/hr through a narrow (15 mm) hot zone in a vertical furnace with peak temperature of $T_{\max}=650^{\circ}\text{C}$. The temperature distribution, T (in $^{\circ}\text{C}$), as a function of distance, x (mm), from the hottest point of the zone was adjusted to follow the cubic parabola form:

$$T(x) \approx T_{\max} - 0.14|x|^3, \text{ for } |x| < 15 \text{ mm.}$$

For the control experiment, some as-deposited films were heated under isothermal conditions at 600°C for 60 min.

Ellipsometry measurements of the residual layers ^[21] on the Si wafer after BaTiO_3 was selectively stripped off suggesting that no significant chemical reaction between Si and BaTiO_3 occurred during film deposition and heat treatment. BaTiO_3 was selectively stripped off with a 15% solution of $(\text{NH}_3)_2\text{Ce}(\text{NO}_3)_6$. Silicates and silicon oxide are not soluble in $(\text{NH}_3)_2\text{Ce}(\text{NO}_3)_6$ and therefore would be easily detected by ellipsometry if formed at the Si/ BaTiO_3 interface. This method cannot distinguish between the oxide grown due to the chemical reaction during the heat treatment and the oxide produced by $(\text{NH}_3)_2\text{Ce}(\text{NO}_3)_6$ (~5 nm) during the film stripping.

As-deposited BaTiO_3 films were stress-free ($< \pm 30 \text{ MPa}$) with refractive index in the range of $n_{\perp}=1.97\div 2.02$, and a very small in-plane-out-of-plane birefringence of $n_{\parallel}-n_{\perp}=-(0.002\div 0.008)$, confirming film isotropy. The refractive index and birefringence were deduced from ellipsometry with fixed wavelength of $\lambda=634 \text{ nm}$ at four different incidence angles ($55\text{-}70^{\circ}$).

A compressive stress of $\sigma_e=2.0\text{-}2.2 \text{ GPa}$ was developed in the films passed through the temperature gradient. The stress was measured by the substrate curvature method ^[22]. The refractive index of these films decreased to $n_{\perp}=1.89\div 1.94$ but the birefringence grew to $n_{\parallel}-n_{\perp}=0.03\div 0.07$, corroborating the existence of high in-plane compressive stress.

All prepared films were analyzed by X-Ray powder diffraction (XRD, Rigaku corp. $\text{CuK}_{\alpha}=1.5405 \text{ \AA}$ - 2θ mode and the pole-figure technique) and by transmission electron microscopy (TEM Phillips CM-120) combined with

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electron diffraction(ED). Scanning electron microscopy (Philips XL30 ESEM-FEG) was employed to image film surfaces and cross sections.

The inventor has further investigated three types of films of the as-deposited amorphous BaTiO₃:

- 5 1) dense, smooth and uniform films;
- 2) films with a large number of structural defects and/or large surface roughness; and
- 3) films deposited on a MgO seeding layer.

10 The conclusion of such experiments was that quasi-amorphous state forms preferably if dense, smooth and uniform films are pulled through the temperature gradient.

Fig. 2A illustrates the X-Ray diffraction spectra of BaTiO₃ films as deposited on (100) Si (1) in comparison to the spectra of the films passed through the temperature gradient (2) and part of the film (1) heated under isothermal
15 conditions (3). The vertical lines correspond to the standard XRD pattern of tetragonal BaTiO₃ (ICSD Collection Code 23758). As shown, X-Ray diffraction (XRD) spectra of the films passed through the temperature gradient are indistinguishable from those of as-deposited films. No XRD peaks apart from those of Si-substrate were observed, indicating the absence of a crystalline phase. The
20 volume detection limit of a crystalline phase by XRD calculated from the signal to noise ratio ^[10] was less than 0.3 %.

Fig. 2B shows the transmission electron microscopy (TEM) image and electron diffraction (ED) pattern of a BaTiO₃ film passed through the temperature gradient. Thus, thorough transmission electron microscopy (TEM) investigation
25 only rarely detected the presence of crystalline grains ^[11] and the concentration of the crystallites estimated from TEM images was far below 0.3%. In contrast to the similarity with respect to electron and X-ray diffraction analysis, as-deposited films and the films passed through the temperature gradient have distinctly different electrical properties.

Fig. 3A shows the pyroelectric response of a $182(\pm 10)$ nm thick amorphous BaTiO₃ film passed through the temperature gradient, to periodic heating by an infra-red laser. The Si substrate is 275 μ m thick; therefore, constant temperature establishes within about 0.2 msec after the laser switches on and off. The films
 5 passed through the temperature gradient show a large pyroelectric effect $p_{measured} = (1-3) \times 10^{-9}$ C/(cm²×K) (5-15% that of a single crystal of BaTiO₃), which remains invariable ($\pm 15\%$) over the temperature range 20-150°C. The time dependence of the electrical current generated by periodical heating has a perfectly symmetric shape, which is a signature for the pyroelectric effect and excludes
 10 possible misinterpretations.

It should be noted that asymmetric contacts may cause a thin film with a strong dependence of the dielectric constant on temperature to appear pyroelectric. The apparent pyroelectric coefficient of this false pyroelectricity can be related to the contact potential difference, D , the dielectric constant, ϵ , the temperature
 15 coefficient of the dielectric constant, $b = 1/\epsilon \times d\epsilon/dT$, and the film thickness, t , as $p = D b \epsilon \epsilon_0 / t$. ϵ_0 denotes dielectric permittivity of vacuum. For the film under consideration this value is order of 10^{-12} C/(cm² K), which is three orders of magnitude below the measured values.

The pyroelectric effect was confirmed independently by the continuous
 20 temperature ramping technique. The direction of the pyroelectric current indicates that the pyroelectric vector is directed toward the substrate. Application of an external electric field of ± 200 kV/cm does not alter the value or the sign of the pyroelectric current, demonstrating that the direction of the pyroelectric vector cannot be changed or reversed (absence of switching).

Fig. 3B shows the temperature dependence of the dielectric constant (at 1
 25 kHz) for amorphous BaTiO₃ thin film; (1) as-deposited film and (2) amorphous film passed through the temperature gradient. The dielectric constant was measured by an Alpha dielectric analyzer (Novocontrol Inc.) with sputtered Cr (300nm) top electrodes. The dielectric constant of the films passed through the

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temperature gradient increases monotonically with temperature from $\approx 30(\pm 3\%)$ at 115 K to $\approx 31(\pm 4\%)$ at 400 K without discontinuities or abrupt slope changes. The dielectric constant shows only minor variations with frequency ($< 4.5\%$) in the $1-10^5$ Hz frequency range and the dielectric loss is less than 0.02. As-deposited
5 BaTiO₃ films do not show any signs of pyroelectricity and have a dielectric constant $\approx 9^{[12]}$, with no significant temperature dependence (Fig. 3B).

The films passed through the temperature gradient exhibit a piezoelectric effect of magnitude $d_{33}=10(\pm 50\%)$ pm/V (5-10% of a single crystal of BaTiO₃), as measured by the two independent techniques. Pyroelectric and piezoelectric
10 effects comprising 5-15% of the corresponding values for a single crystal cannot be explained by inclusions of crystallites (less than 0.3%) and thus originate from the highly stressed amorphous phase formed in the films passed through the temperature gradient.

The periodic temperature change technique ^[23,24] with a semiconductor
15 laser as a heat source ^[25] and a continuous temperature ramping method ^[26] were used to determine the film pyroelectric coefficient. Piezoelectric coefficient was evaluated from Piezoelectric Force Microscopy (PFM) data (MMAFM, DI-VEECO)^[27]. The measurement was performed using the signal access module to which a sinusoidal voltage was applied to the tip at 5 - 15 kHz, and the resultant
20 tip response monitored with a lock-in amplifier and by a single path interferometer with a calibrated reference standard (single crystal LiNbO₃). For the latter, the sample was indium-soldered to a 5mm thick copper plate to avoid substrate bending.

Subjecting the films passed once through the temperature gradient to up to
25 three such additional cycles did not alter their properties. Isothermal heating (600°C 2 hrs, 680°C 1.5 hrs, 800°C 20 min.) also leaves their properties unchanged. Above 800°C, the BaTiO₃ reacts with Si forming barium silicates^[13].

Figs. 4A and 4B show scanning electron microscopy images (secondary electron mode) of, respectively, an amorphous BaTiO₃ thin film passed through

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the temperature gradient; the other part of the same amorphous films heated in isothermal conditions. In these experiments, the as-deposited BaTiO₃ films formed polycrystalline BaTiO₃ following isothermal heating for 1 hr at 600°C. The refractive index of these films is quite low $n_{\perp} = n_{\parallel} = 1.80 \div 1.85$ ^[14] and the
5 compressive stress of 0.2-0.6 GPa is significantly smaller than that of the films passed through the temperature gradient, as described above. The true pyroelectric effect or stress-induced pyroelectric effect will appear only if the material has no center of symmetry, i.e., the sub-nanocrystalline material has to have an assymetric preferred direction. Thus, the sub-nanocrystalline material
10 has a local order resulting in appearance of spontaneous polarization. The relatively high thermal stability of the sub-nanocrystalline state and its high birefringence ($n_{\perp} - n_{\parallel} = -(0.03 \div 0.07)$) can be explained by the short-range, stress-induced dipole ordering, similar to what was earlier observed in crystals²⁸. Such effects for anisotropic media were considered in the past²⁹, however, attempts to
15 produce a clear pyroelectric signature from a nearly disordered material remained illusive³⁰, giving only indirect evidence of the presence of spontaneous polarization. The experiments conducted by the inventor have shown that short-range dipole ordering in the sub-nanocrystalline material is stress-induced and appears during passing the films through the temperature gradient.

CLAIMS:

1. An inorganic, quasi-amorphous oxide compound of a metal, mixture of metals or semiconducting element, said compound having pyroelectric properties.
2. The compound of claim 1 having the formula $(A_xB_{1-x})_pO_n$, wherein A and B
5 are independently selected from transitions metals, elements of Group IVA of the periodic table, alkali metals, alkali earth metals and rare earth metals; x has values of between 0 to 1; p is an integer having the values 1, 2 or 3; and n is an integer having the value of 1, 2, 3 or 4.
3. The compound of claim 2, wherein A is a transition metal or an element of
10 Group IVA of the periodic table, x is 1 and p is 2.
4. The compound of claim 1, having the formula $(A_xB_{1-x})(C_yD_{1-y})O_n$ wherein A and B are independently selected from alkali metals, alkali earth metals, rare earth metals and elements of Group IVA of the periodic table; C and D are independently selected from transition metals and alkali earth metals; x and y have
15 values of between 0 to 1; and n is an integer having the value of 1, 2 or 3.
5. The compound of claim 4, wherein A and B are independently selected from Ba, Sr, Ca, Pb, La, Eu, Li, Na, K and Cs ; C and D are independently selected from Ti, Zr, Nb, Ta, Sc, Mg and V; and n is 3.
6. The compound of claim 5, wherein A and B are independently selected
20 from Ba, Sr, Ca, Pb, La and Eu.
7. The compound of claim 5, wherein A and B are independently selected from Li, Na, K and Cs.
8. The compound of claim 5, wherein C and D are independently selected from Ti and Zr.
9. The compound of claim 6, wherein C and D are independently selected
25 from Ti and Zr.
10. The compound of claim 7, wherein C and D are independently selected from Ti and Zr.

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11. The compound of claim 5, wherein C and D are independently selected from Nb, Ta, Sc, Mg and V.

12. The compound of claim 6, wherein C and D are independently selected from Nb, Ta and V.

5 13. The compound of claim 7, wherein C and D are independently selected from Nb, Ta and V.

14. The compound of claim 4, wherein $y=0$ and having the formula $(A_xB_{1-x})DO_3$, wherein A, B, D and x are as defined in claim 4.

15 15. The compound of claim 4 having a pyroelectric coefficient of between about 10^{-12} C/(cm² x K) and about 10^{-7} C/(cm² x K).

16. The compound of claim 14 having a pyroelectric coefficient of between about 10^{-12} C/(cm² x K) and about 10^{-7} C/(cm² x K).

17. The compound of claim 4 selected from BaTiO₃, CaTiO₃, PbTiO₃, Pb(ZrTi)O₃, Pb(Zr_{0.35}Ti_{0.65})O₃, (PbCa)TiO₃, (PbLa)(ZrTi)O₃, PbLaTiO₃,
15 Pb(ScTa)O₃, Pb(ScNb)O₃, Pb(MgNb)O₃, SrTiO₃, (Sr_{0.65}Ba_{0.35})TiO₃, (Ba_{0.70}Sr_{0.30})TiO₃ and EuTiO₃.

18. The compound of claim 17 having a pyroelectric coefficient of between about 10^{-12} C/(cm² x K) and about 10^{-7} C/(cm² x K).

19. The compound of claim 17 being selected from BaTiO₃, PbTiO₃ and
20 SrTiO₃.

20. The compound of claim 18 being BaTiO₃.

21. A process for preparing pyroelectric compound, comprising applying a mechanical strain to a substantially amorphous compound of the formula $(A_xB_{1-x})(C_yD_{1-y})O_n$ as defined in claim 4, said mechanical strain being controlled so as to
25 prevent crystallization of said compound, thereby obtaining inorganic quasi-amorphous compound having pyroelectric properties.

22. The process of claim 21, wherein said mechanical strain is obtained by a temperature gradient.

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23. The process of claim 21, wherein said amorphous compound has the formula $(A_xB_{1-x})DO_3$, wherein A, B, D and x have the meanings as defined in claim 14.

24. Inorganic quasi-amorphous compound of the formula $(A_xB_{1-x})(C_yD_{1-y})O_3$ as defined in claim 14 preparable by the process of claim 21.

25. A device comprising the compound according to claim 1 in the form of a film coating on a substrate.

26. A device comprising the compound according to claim 4 in the form of a film coating on a substrate.

27. The device of claim 26, wherein the substrate is selected from Si, SiO_2 and glass.

28. The device of claim 27, wherein the thickness of the coating layer is below 0.5 micron.

29. A device comprising the compound of claim 1, the device being operable as a sensor for sensing an external field including at least one of the following: temperature field, magnetic field and electric field.

30. A device comprising the compound of claim 4, the device being operable as a sensor for sensing an external field including at least one of the following: temperature field, magnetic field and electric field.

31. A device having an acoustic wave propagation element including the compound of claim 1.

32. A device having an acoustic wave propagation element including the compound of claim 4.

33. A device having an acoustic wave propagation element including the compound of claim 5.

34. A birefringent medium comprising the compound of claim 1.

35. A birefringent medium comprising the compound of claim 4.

36. A device comprising the compound according to claim 1.

37. A device comprising the compound according to claim 4.

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38. A device comprising a compound according to claim 3 in the form of a film coating on a substrate.

39. The device of claim 38, wherein the substrate is selected from Si, SiO₂ and glass.

5 **40.** The device of claim 39, wherein the compound is SiO₂.

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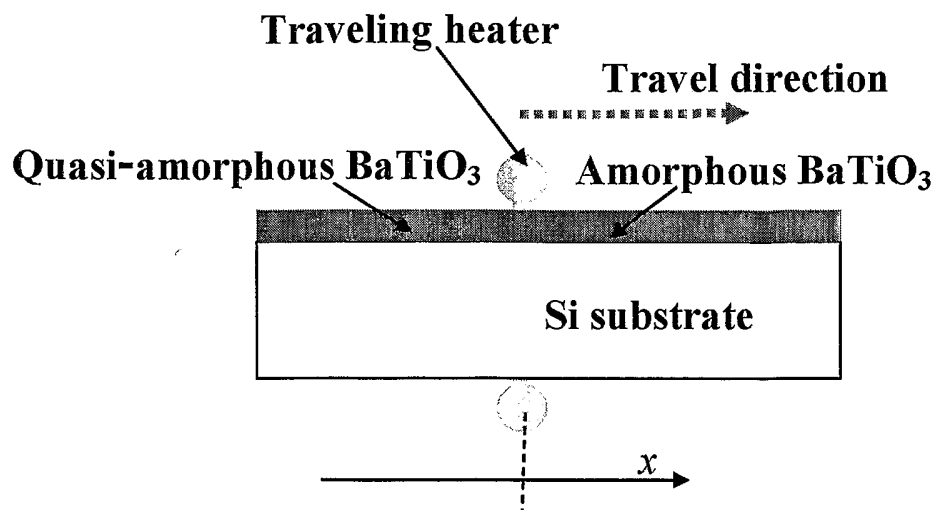


FIG.1

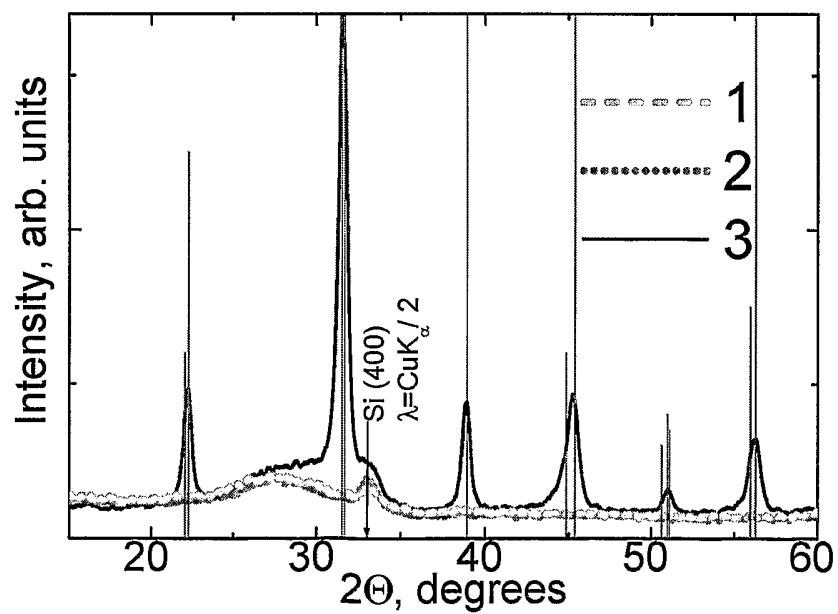


FIG. 2A

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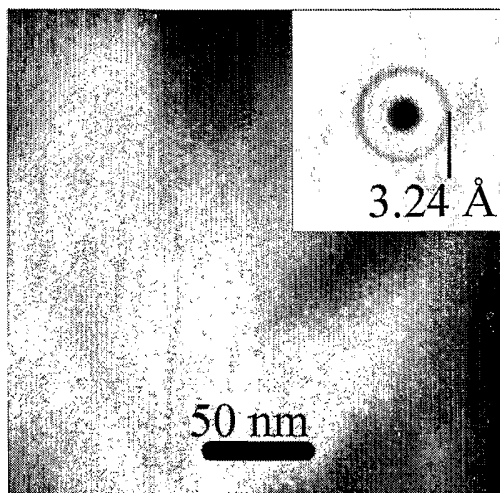


FIG.2B

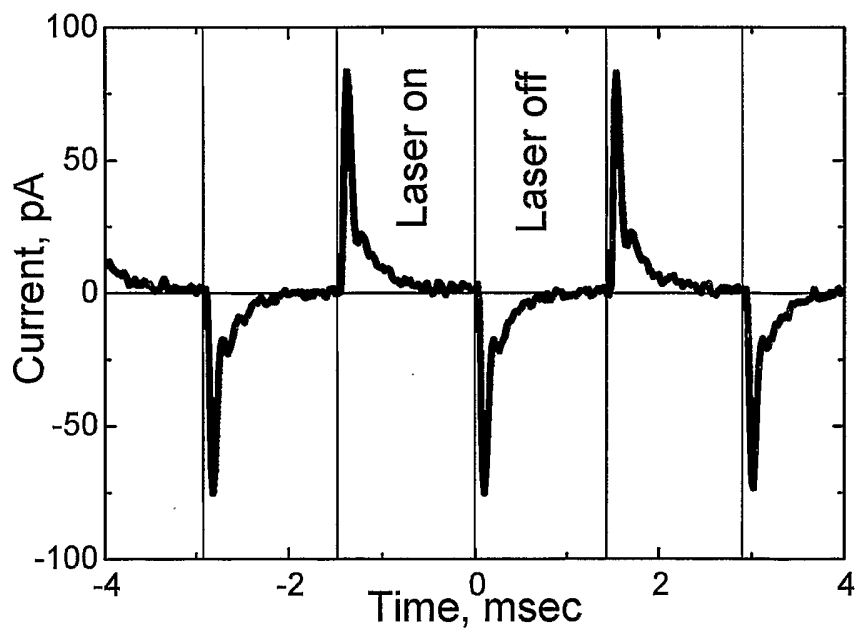


FIG. 3A

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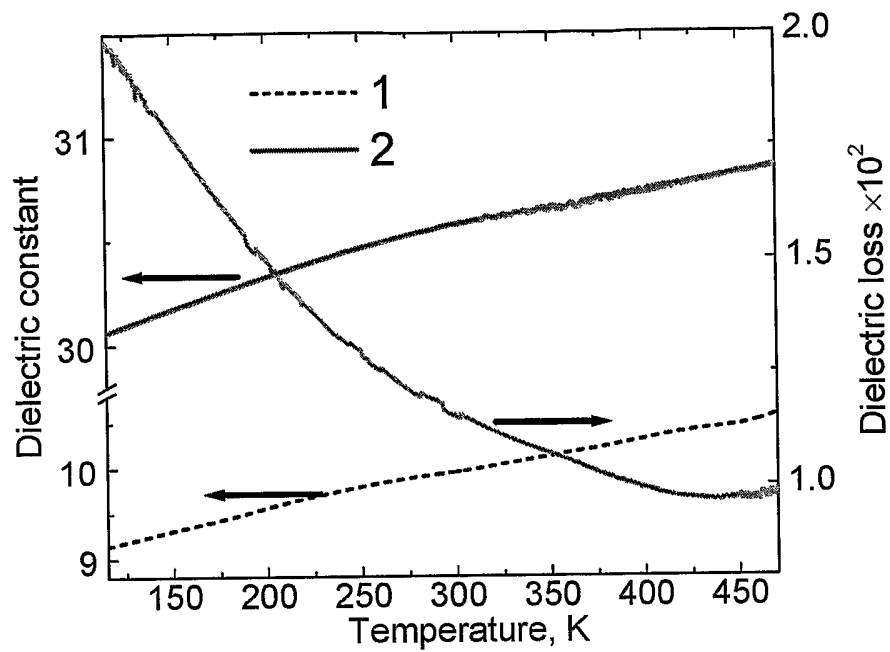


FIG.3B

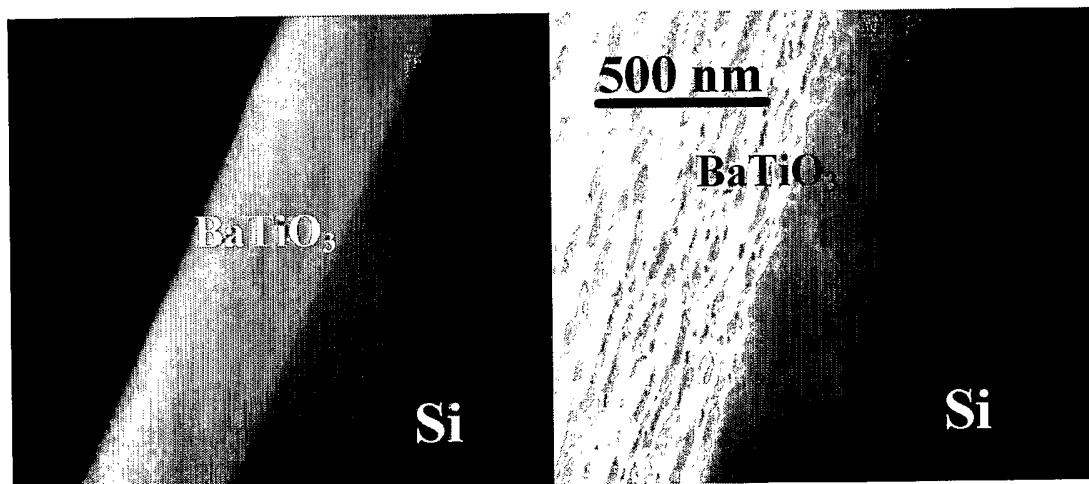


FIG. 4A

FIG. 4B